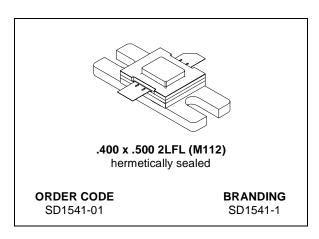


# SD1541-01

# RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

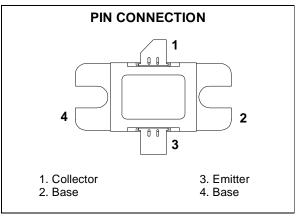
- DESIGNED FOR HIGH POWER PULSED IFF AND DME APPLICATIONS
- 400 W (min.) DME 1025 1150 MHz
- 6.5 dB min. GAIN
- REFRACTORY GOLD METALLIZATION
- EMITTER BALLASTING AND LOW THERMAL RESISTANCE FOR RELIABILITY AND RUGGEDNESS
- 30:1 LOAD VSWR CAPABILITY AT SPECIFICIED OPERATING CONDITIONS
- INPUT/OUTPUT MATCHED, COMMON BASE CONFIGURATION



#### **DESCRIPTION**

The SD1541-01 is a hermetically sealed, gold metallized, silicon NPN power transistor. The SD1541-01 is designed for applications requiring high peak power and low duty cycles such as DME.

The SD1541-01 is packaged in a hermetic metal/ceramic package with internal input/output matching, resulting in improved broadband performance and a low thermal resistance.



# **ABSOLUTE MAXIMUM RATINGS** (T<sub>CASE</sub> = 25 °C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	65	V
V <sub>CES</sub>	Collector-Emitter Voltage	65	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V
Ic	Device Current	22	Α
P <sub>DISS</sub>	Power Dissipation	1458	W
Tj	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

# THERMAL DATA

R <sub>th(j-c)</sub>	Junction -Case Thermal Resistance	0.12	°C/W

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# **ELECTRICAL SPECIFICATION** (T<sub>CASE</sub> = 25 °C)

#### **STATIC**

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
BV <sub>CBO</sub>	$I_C = 25mA$ $I_E = 0mA$	65			٧
BV <sub>EBO</sub>	$I_E = 10 \text{mA}$ $I_C = 0 \text{mA}$	3.5			V
BV <sub>CES</sub>	$I_C = 50 \text{mA}$ $V_{BE} = 0 \text{V}$	65			V
I <sub>CES</sub>	$V_{CE} = 50V$ $I_E = 0mA$			25	mA
h <sub>FE</sub>	$V_{CE} = 5V$ $I_C = 0.25A$	5		200	

#### **DYNAMIC**

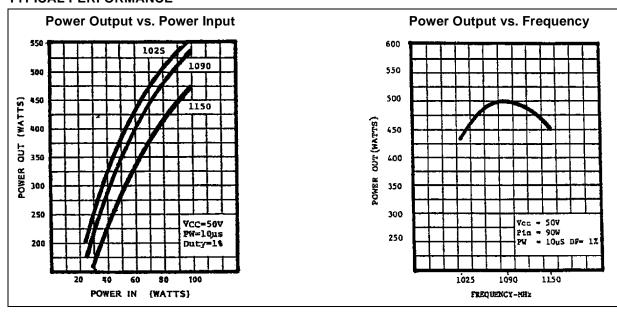
Symbol	Test Conditions	Min.	Тур.	Max.	Unit
P <sub>OUT</sub>	f = 1025 - 1150 MHz   P <sub>IN</sub> = 90 W   V <sub>CE</sub> = 50 V	400			W
G <sub>P</sub>	f = 1025 - 1150 MHz	6.5			dB

Note: Pulse width = 10  $\mu$ s, Duty Cycle = 1%

This device is suitable for use under pulse width/duty cycle conditions.

Please contact the factory for specific applications assistance.

# **TYPICAL PERFORMANCE**

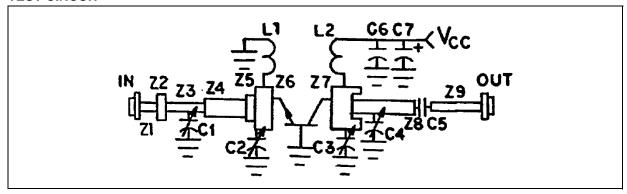


#### **IMPEDANCE DATA**

FREQ. MHz	<b>Z</b> <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)
1020	2.5 + j 3.2	1.6 - j 2.5
1090	2.2 + j 4.5	1.5 - j 2.7
1150	3.7 + j 2.1	1.3 - j 1.5

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# **TEST CIRCUIT**

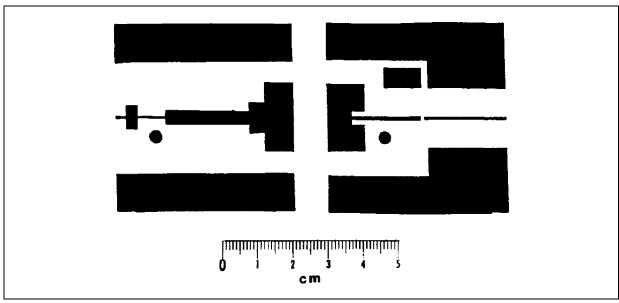


## **COMPONENT PART LIST**

COMPONENT	DESCRIPTION
C1	0.4 - 2.5pF Johanson Gigatrim
C2, C3, C4	0.6 - 4.5pF Johanson Gigatrim
C5	82pF Chip Capacitor, 0.055 Sq.
L1	Loop, #18 Tinned, 0.36 Wide x 0.27 above Circuit
L2	4 3/4 Turns, #24 Enameled, Close Wound, 0.075 I.D.
Z1	50 Ω (0.02 Wide)
<b>Z</b> 2	0.250 x 0.120
Z3	50 Ω 0.020 x 0.330; C1 tapped 0.15 from Load
Z4	0.145 x 0.920
Z5	0.325 x 0.180
Z6	0.730 x 0.315
<b>Z</b> 7	0.710 x 0.425 with 0.140 x 0.150 cutout
Z8	0.035 x 0.780; C4 Tapped 0.36 from Cen
<b>Z</b> 9	50 Ω
BOARD	3M EPSILAM10, 0.032 THK., 1 OZ

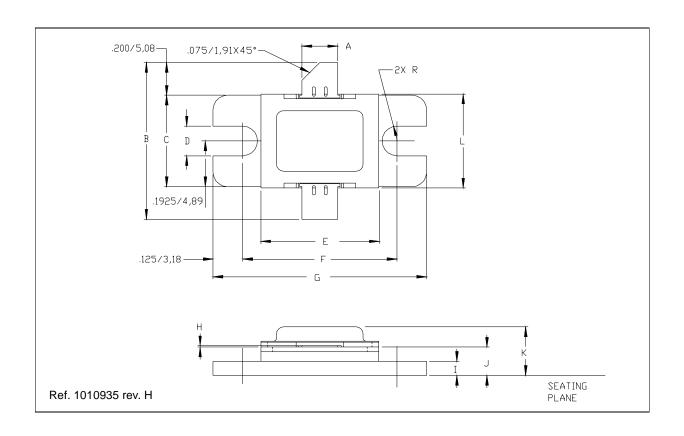
Note: All Dimensions in Inches Unless Otherwise specified C1, C4 Cold End Terminated Through Eyelet.

## **PC BOARD LAYOUT**



# M112 (.400 x .500 2LFL) MECHANICAL DATA

DIM.		mm			Inch	
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
А	3.68		3.93	0.145		0.155
В	19.56		21.08	0.770		0.830
С	9.65		9.91	0.380		0.390
D	3.05		3.43	0.120		0.135
E	12.57		12.88	0.495		0.507
F	16.26		16.64	0.640		0.655
G	22.73		22.99	0.895		0.905
Н	0.05		0.15	0.002		0.006
I	1.40		1.65	0.055		0.065
J	2.79		3.30	0.110		0.130
K			5.84			0.230
L	10.03		10.34	0.395		0.407



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